/ Descriptions

SiC

/ Features

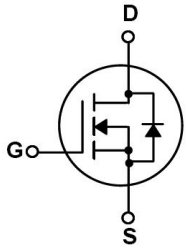
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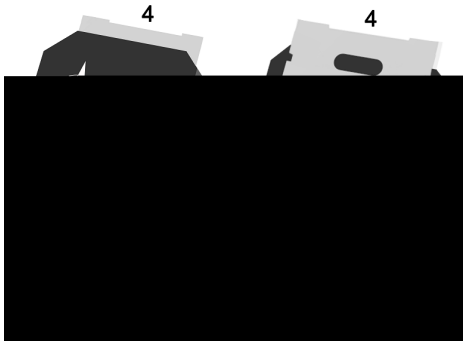
/ Applications

LED PD PC

/ Equivalent Circuit



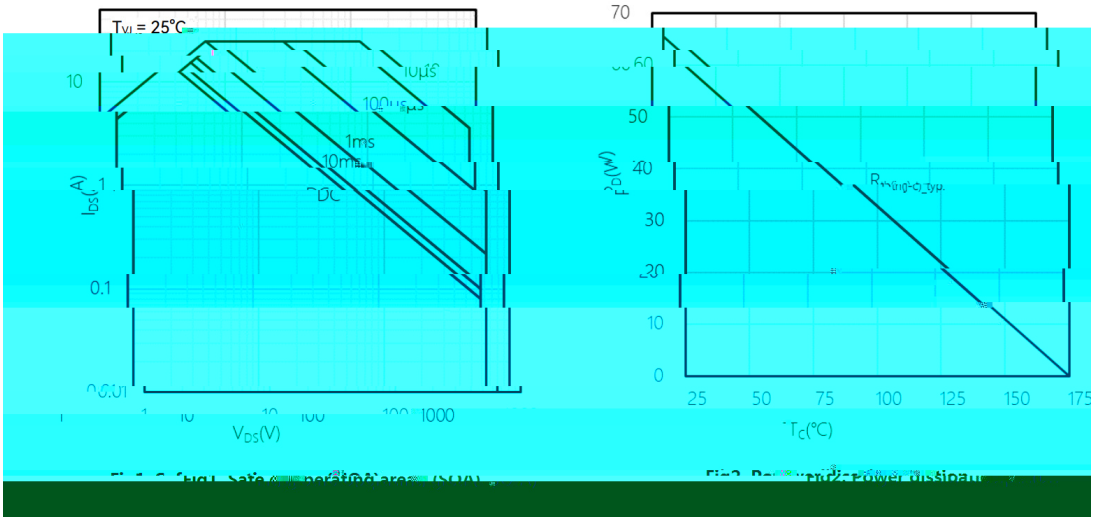
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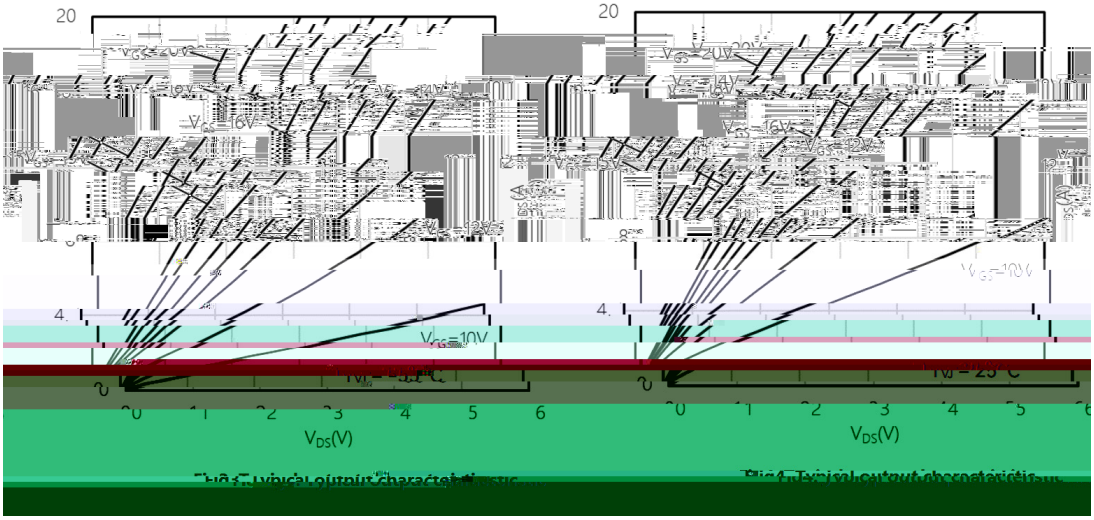


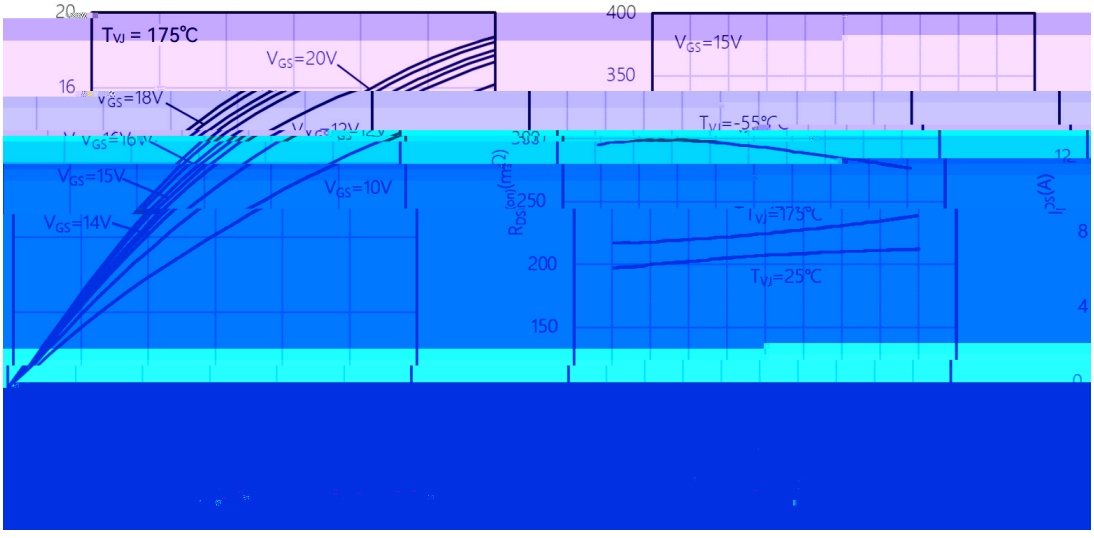
/ Marking

BRSC65R260ZDP

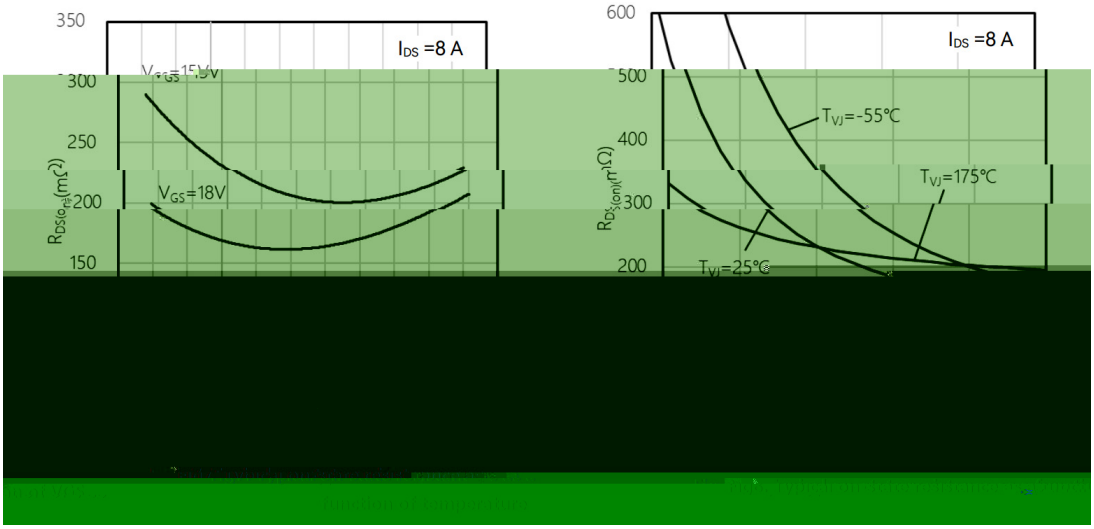
/ Electrical Characteristic Curve







/ Electrical Characteristic Curve



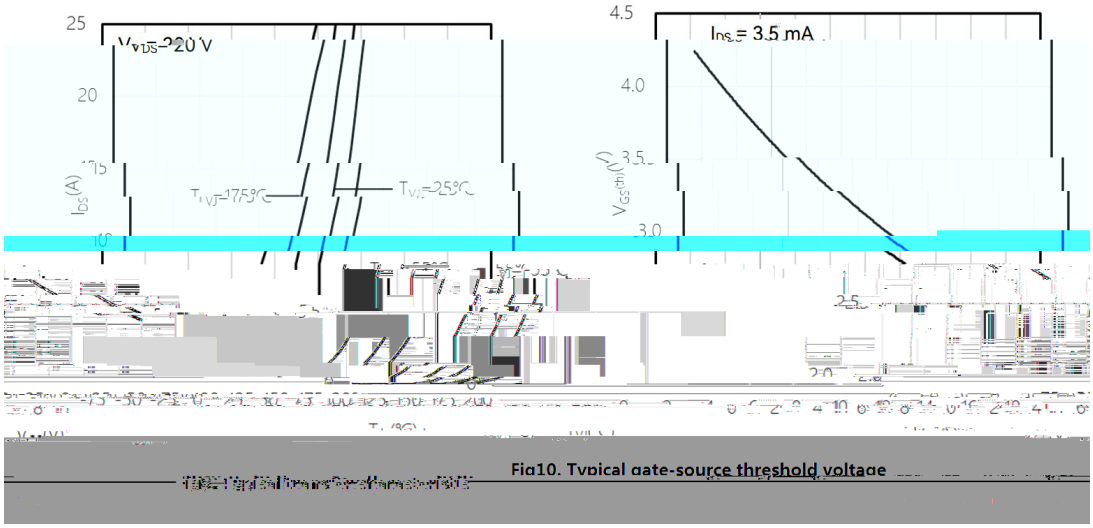
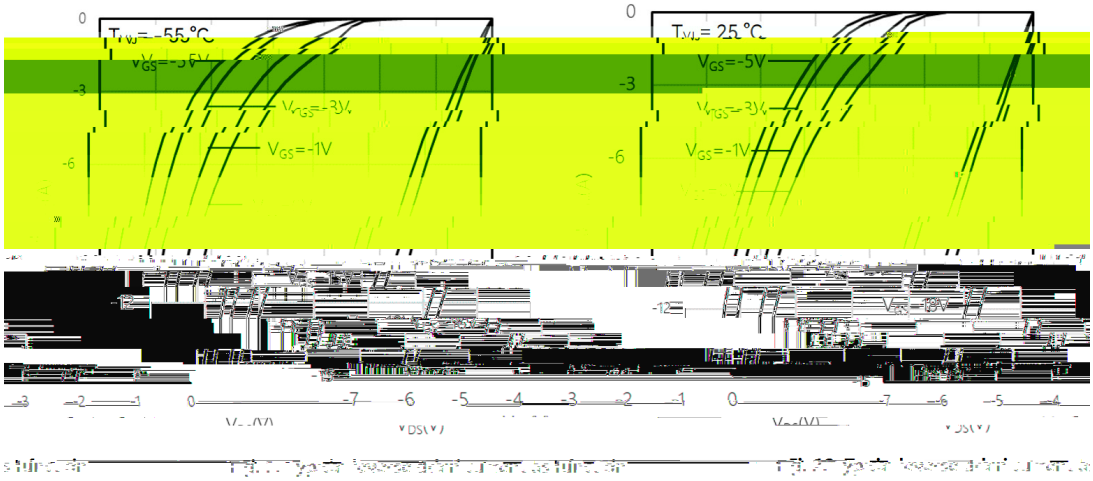


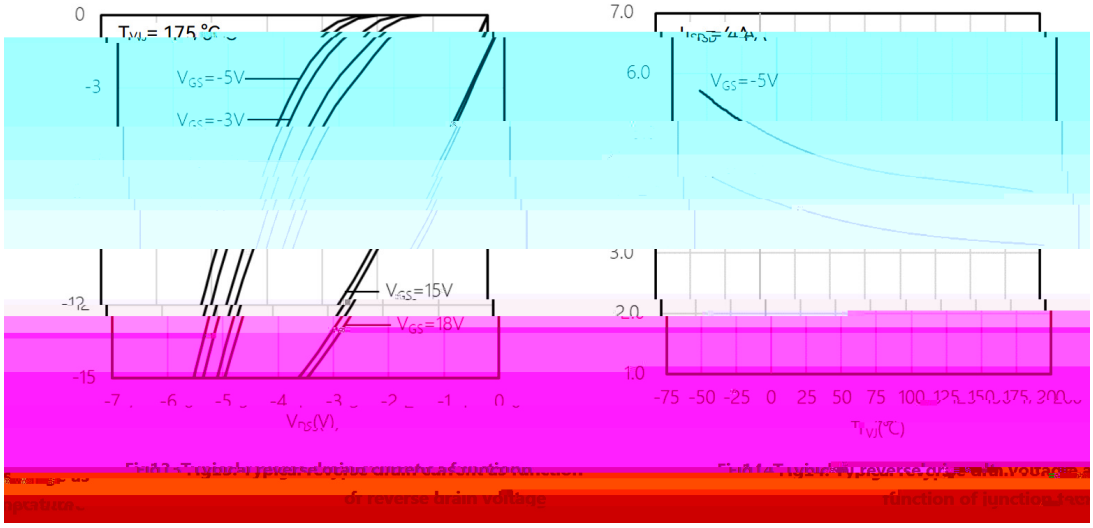
Fig10. Typical gate-source threshold voltage

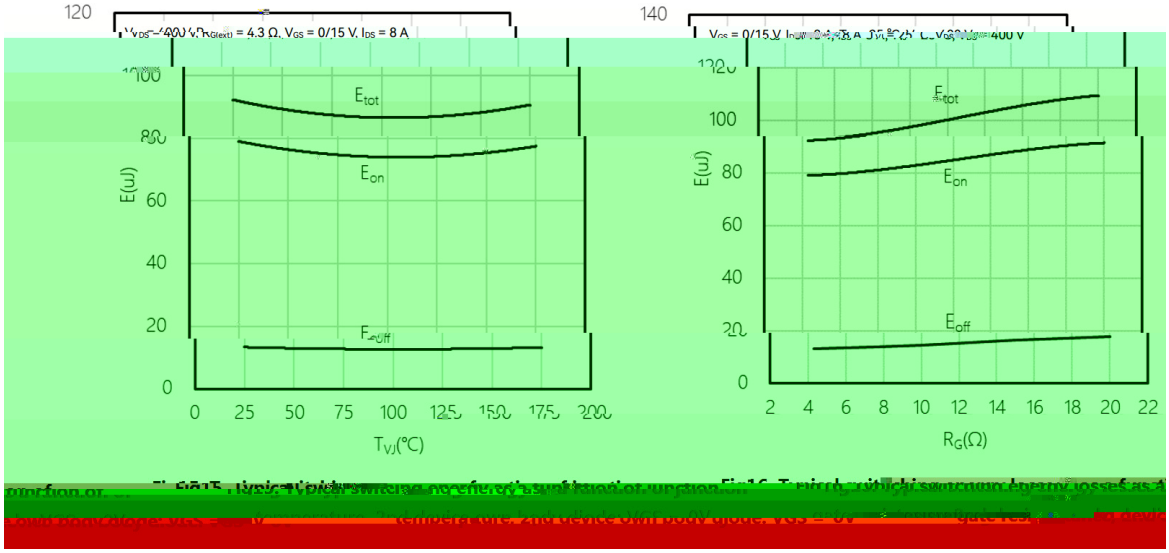


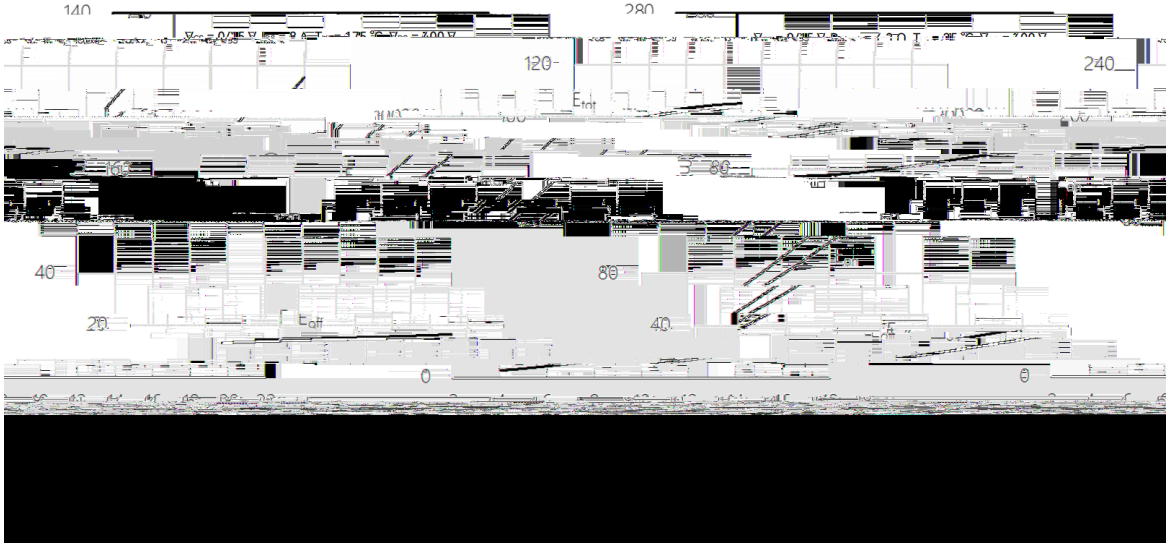
of reverse drain voltage

of reverse drain voltage

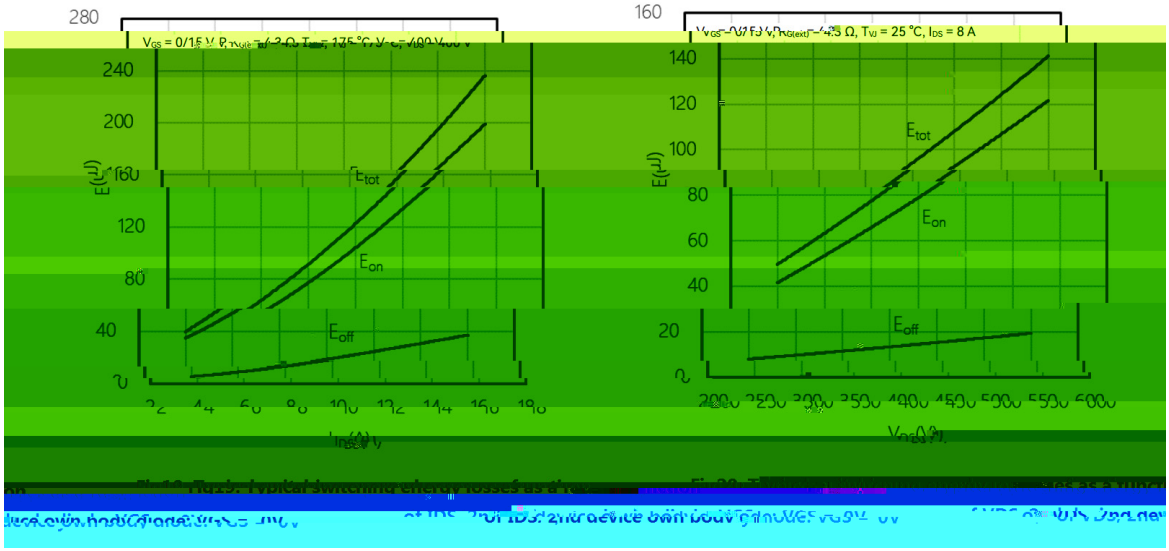
/ Electrical Characteristic Curve







/ Electrical Characteristic Curve



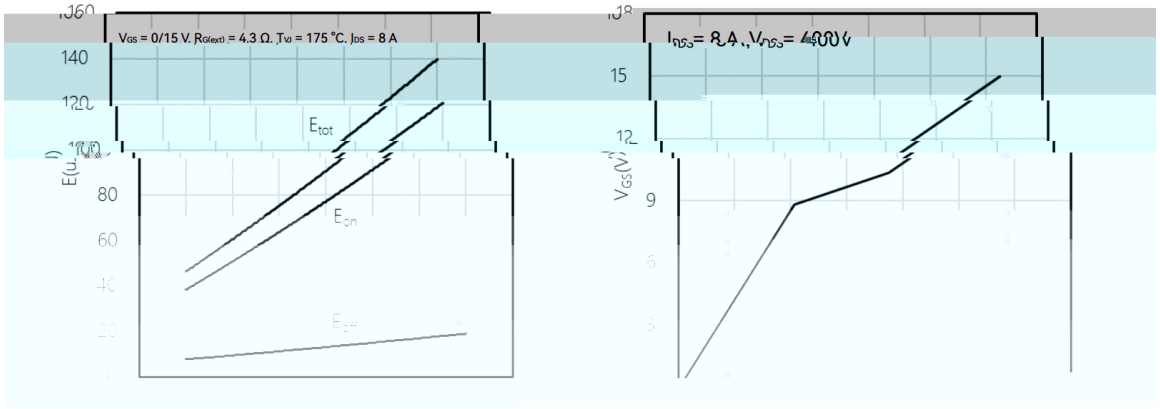


Fig21. Typical switching energy losses as a function of VDS, 2nd device own body diode: VGS = 0V

Fig22. Typical gate charge

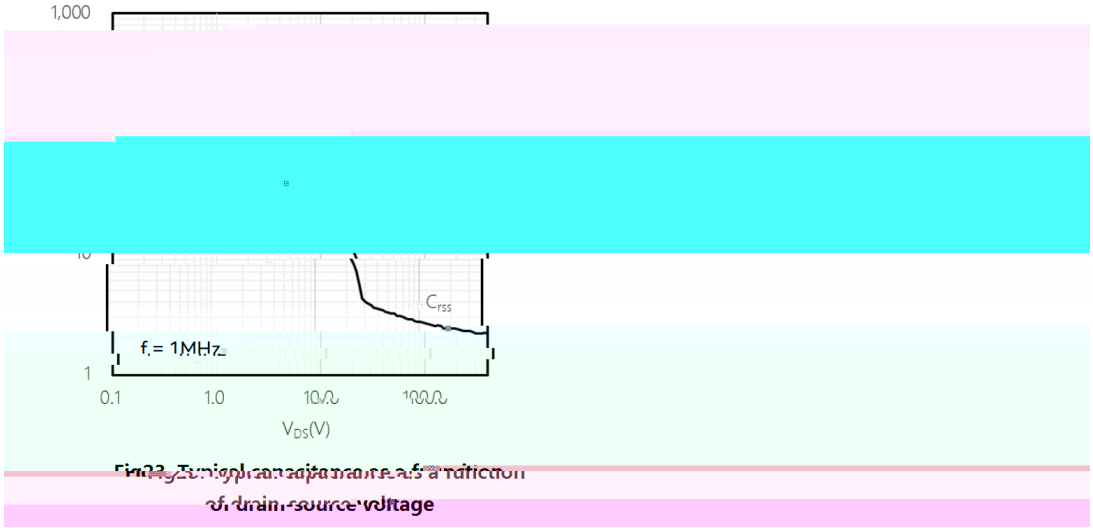


Fig23. Typical capacitance as a function of drain-source voltage

/ Electrical Characteristic Curve

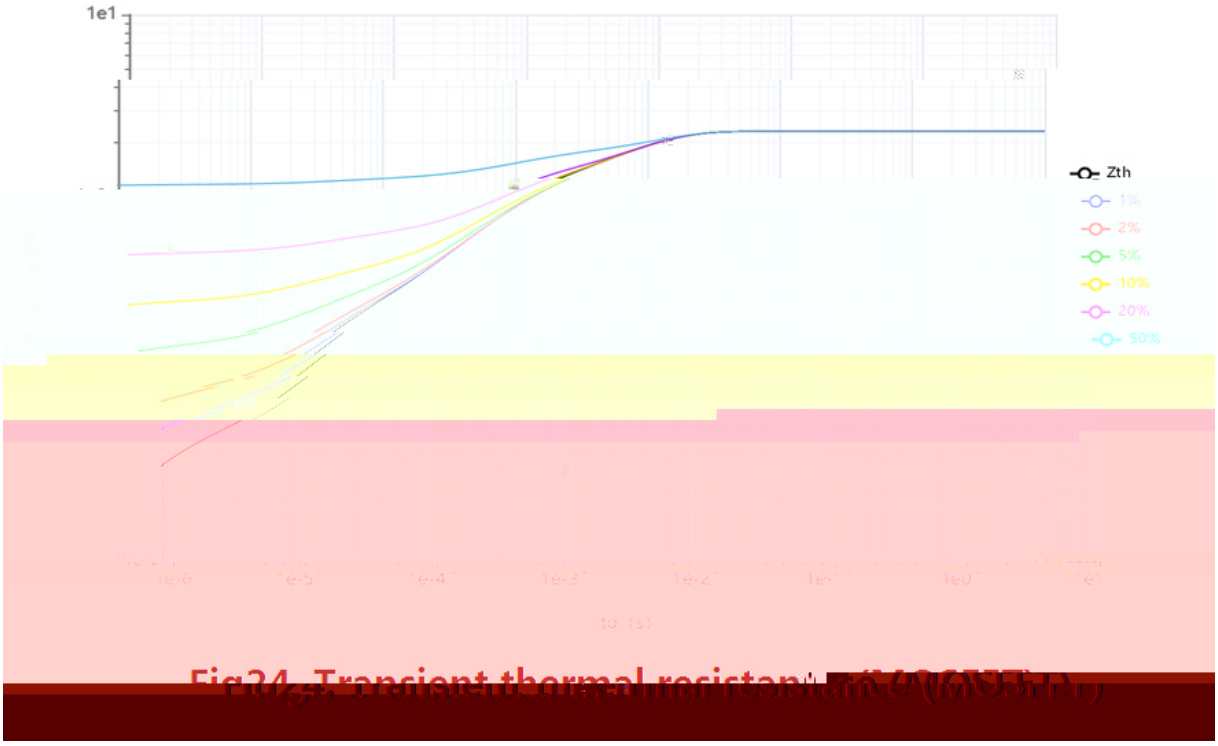
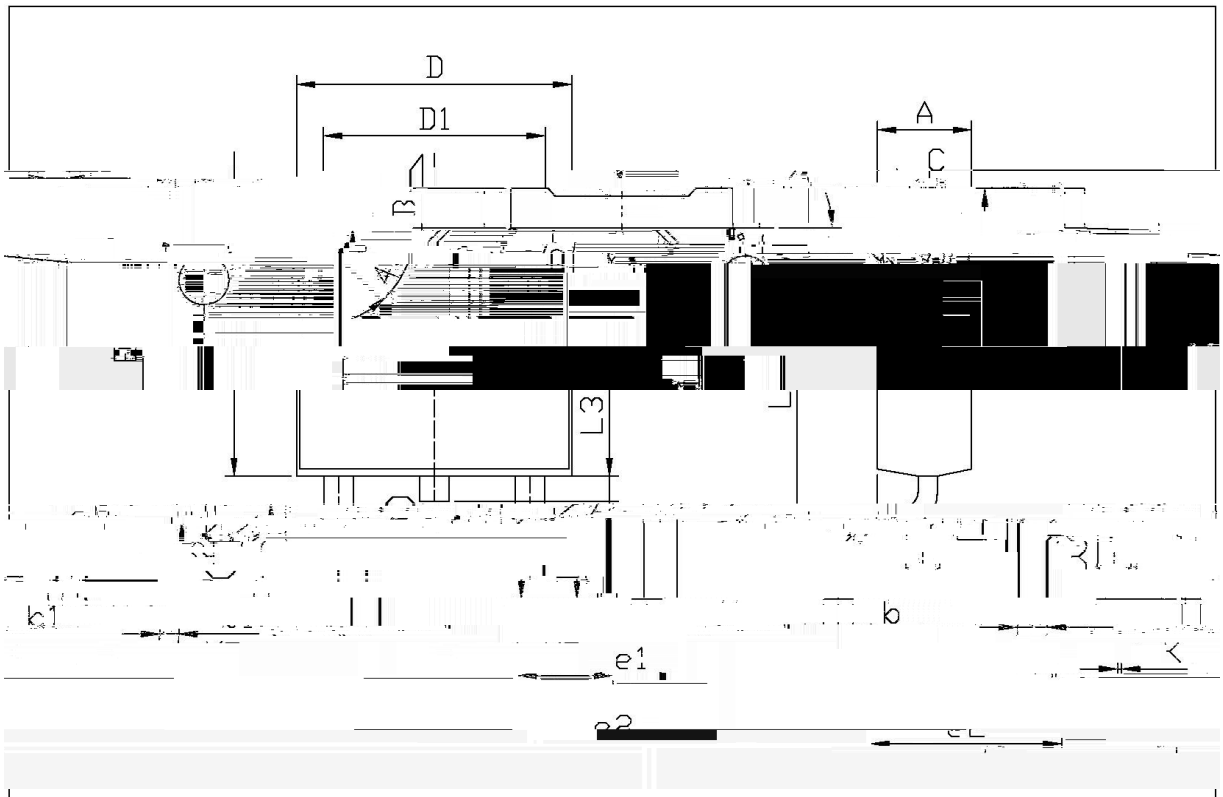


Fig24. Transient thermal resistance(MOSFET)

/ Package Dimensions



单位：mm

Dimensions In Millimeters				Dimensions In Millimeters			
Symbol	Min	Max		Symbol	Min	Max	
A	2.08	2.40		b	0.70	0.90	
b1	0.95	1.25		c	0.40	0.55	
c1	0.40	0.55		D	6.45	6.75	
D1	5.10	5.50		E	6.00	6.20	
e	2.24	2.34		e1	4.42	4.72	
H	9.80	10.30		L	1.40	1.78	
L1	2.90	3.10		L2	1.60	1.80	
L3	0.90	1.25		R	0.50	0.70	
V	5.30	5.50		θ	0°	8°	

TO-252

/ Marking Instructions

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